QNERC Workshop on Nano Devices and Materials
Tuesday, 4th November, 2014
Conference Room 605, Ookayama South-9, Tokyo Institute of Technology

10:00 – 10:10  Shunri Oda/ TIT  Welcome Address
10:40 – 11:05  Mutsuko Hatano/ TIT, Diamond semiconductor devices for power electronics and sensing application.
11:05 – 11:30  Hiroshi Wakabayashi TIT, Advanced-CMOS Device Benchmarks and following Transition-Metal Dichalcogenides (TMDs) for 2D FETs.
11:30 – 11:55  Hiroshi Mizuta/ JAIST, Downscaled graphene nanoelectronic and nano-electro-mechanical (NEM) devices.
(Lunch Break)
13:50 – 14:15  Chuanbo Li/ IoS-CAS, Si/Ge nanomaterials and their device application.
14:40 – 15:05  Zhengyu Xu/ TIT, Impact of gold catalyst evolution on Ge nanowire morphology.
(Coffee Break)
15:50 – 16:15  Tetsuo Kodera/ TIT, Quantum devices using group IV materials.
16:40 – 17:05  David Herbschleb/ Cambridge/TIT, Charge-writing induced quantum devices in graphene.
17:05 – 17:30  Chunlai Xue/ IoS-CAS, Si based Ge and GeSn photodetectors for optical communication and data center.
17:30 – 17:55  Yukio Kawano/ TIT, Nano-carbon devices as an enabler of Terahertz technology.